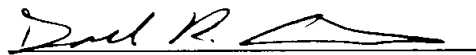


REMARKS

The specification has been amended to correct editorial correction in order to place them in better condition for examination.

Examination on the merits is requested.

Respectfully submitted,



Donald R. Studebaker
Registration No. #32,815

NIXON PEABODY LLP
8180 Greensboro Drive, Suite 800
McLean, Virginia 22102
(703) 770-9300

DRS/sas

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIM:

13. (AMENDED) A method of fabricating a nitride semiconductor device by a vapor deposition method comprising:

a step of growing , on a substrate, a first nitride semiconductor layer including [aluminum and/or] magnesium under a first growth ambient pressure; and

a step of growing a second nitride semiconductor layer, which is adjacent to said first nitride semiconductor layer and does not include aluminum and magnesium, under a second growth ambient pressure,

wherein said first growth ambient pressure is lower than said second growth ambient pressure, and is lower than the atmospheric pressure